

## Silicon Diffused Power Transistor

PHE13009

## GENERAL DESCRIPTION

The PHE13009 is a silicon npn power switching transistor in the TO220AB envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

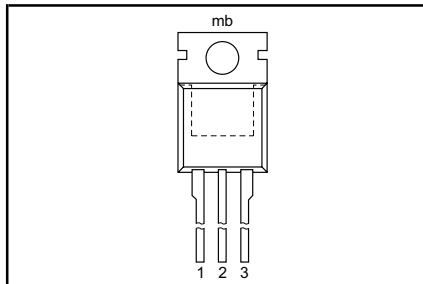
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	700	V
$V_{CBO}$	Collector-Base voltage (open emitter)		-	700	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	400	V
$I_C$	Collector current (DC)		-	12	A
$I_{CM}$	Collector current peak value		-	24	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25\text{ °C}$	-	80	W
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$	0.32	1.0	V
$h_{FEsat}$		$I_C = 5.0\text{ A}; V_{CE} = 5\text{ V}$	-	40	
$t_f$	Fall time	$I_C = 5.0\text{ A}; I_{B1} = 1.0\text{ A}$	0.1	0.5	$\mu\text{s}$

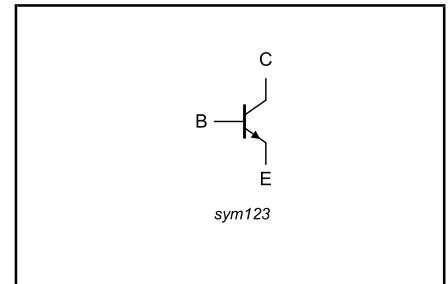
## PINNING - TO220AB

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CESM}$	Collector to emitter voltage	$V_{BE} = 0\text{ V}$	-	700	V
$V_{CEO}$	Collector to emitter voltage (open base)		-	400	V
$V_{CBO}$	Collector to base voltage (open emitter)		-	700	V
$I_C$	Collector current (DC)		-	12	A
$I_{CM}$	Collector current peak value		-	24	A
$I_B$	Base current (DC)		-	6	A
$I_{BM}$	Base current peak value		-	12	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25\text{ °C}$	-	80	W
$T_{stg}$	Storage temperature		-65	150	°C
$T_j$	Junction temperature		-	150	°C

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Junction to mounting base		-	1.56	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	60	-	K/W

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**STATIC CHARACTERISTICS** $T_{mb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CES}, I_{CBO}$ $I_{CES}$	Collector cut-off current <sup>1</sup>	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$	-	-	1.0 5.0	mA mA
$I_{CEO}$ $I_{EBO}$ $V_{CEOsust}$	Collector cut-off current Emitter cut-off current Collector-emitter sustaining voltage	$V_{CEO} = V_{CEOMmax} (400\text{V})$ $V_{EB} = 9\text{ V}; I_C = 0\text{ A}$ $I_B = 0\text{ A}; I_C = 10\text{ mA};$ $L = 25\text{ mH}$	- - 400	- - -	0.1 1 -	mA mA V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$ $I_C = 8.0\text{ A}; I_B = 1.6\text{ A}$	- -	0.32 -	1.0 2.0	V V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C = 5.0\text{ A}; I_B = 1.0\text{ A}$ $I_C = 8.0\text{ A}; I_B = 1.6\text{ A}$	- -	1.0 1.1	1.3 1.6	V V
$h_{FE}$ $h_{FEsat}$	DC current gain	$I_C = 5.0\text{ A}; V_{CE} = 5\text{ V}$ $I_C = 8.0\text{ A}; V_{CE} = 5\text{ V}$	8 6	- -	40 30	

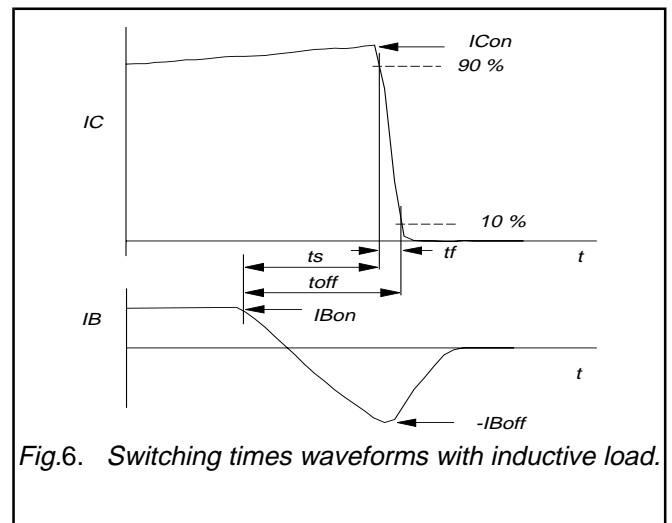
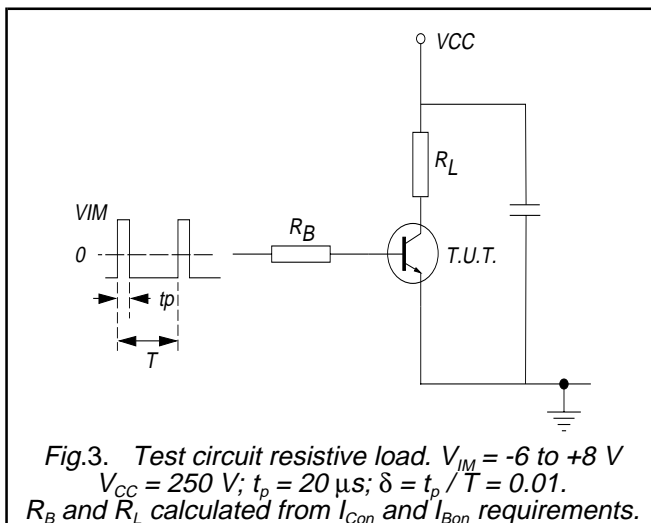
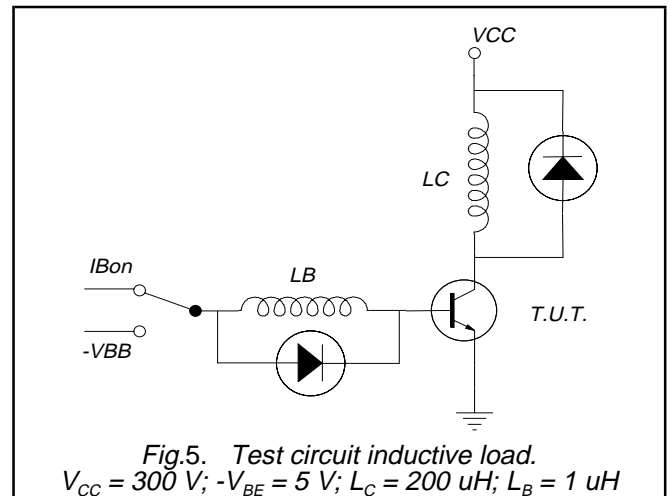
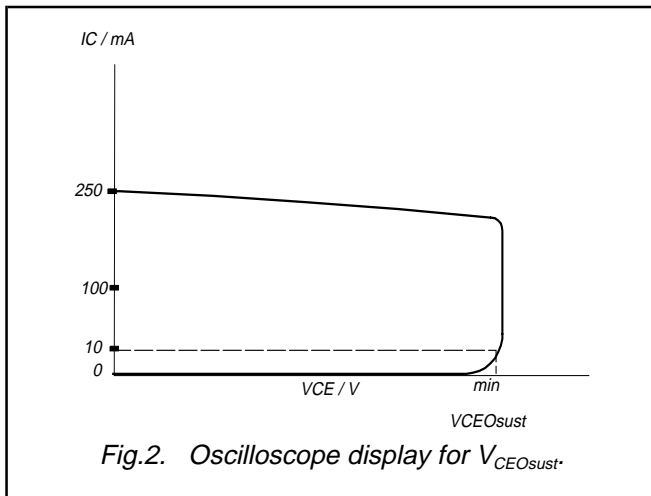
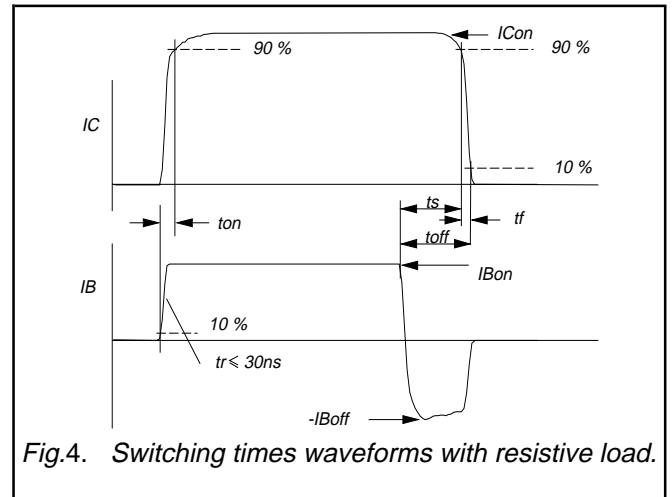
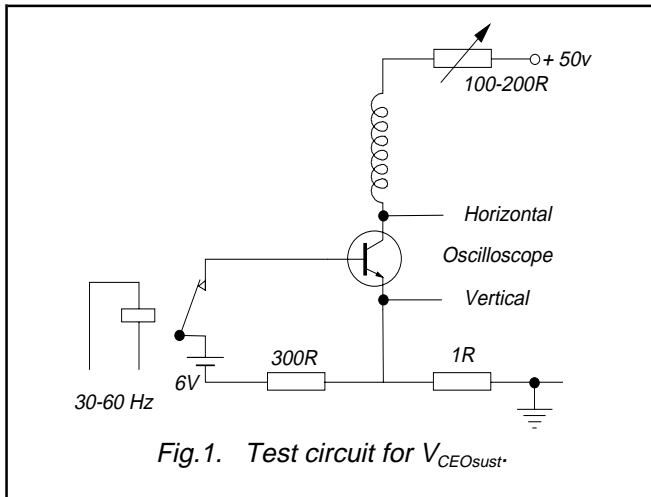
**DYNAMIC CHARACTERISTICS** $T_{mb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (resistive load)	$I_{Con} = 5\text{ A}; I_{Bon} = -I_{Boff} = 1\text{ A};$ $R_L = 75\text{ ohms}; V_{BB2} = 4\text{ V};$			
$t_s$ $t_f$	Turn-off storage time Turn-off fall time		2.2 0.26	3.3 0.7	$\mu\text{s}$ $\mu\text{s}$
	Switching times (inductive load)	$I_{Con} = 5\text{ A}; I_{Bon} = 1\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}$			
$t_s$ $t_f$	Turn-off storage time Turn-off fall time		1.35 0.1	2.3 0.5	$\mu\text{s}$ $\mu\text{s}$
	Switching times (inductive load)	$I_{Con} = 5\text{ A}; I_{Bon} = 1\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}; T_j = 100\text{ }^{\circ}\text{C}$			
$t_s$ $t_f$	Turn-off storage time Turn-off fall time		- -	3.2 0.9	$\mu\text{s}$ $\mu\text{s}$

<sup>1</sup> Measured with half sine-wave voltage (curve tracer).

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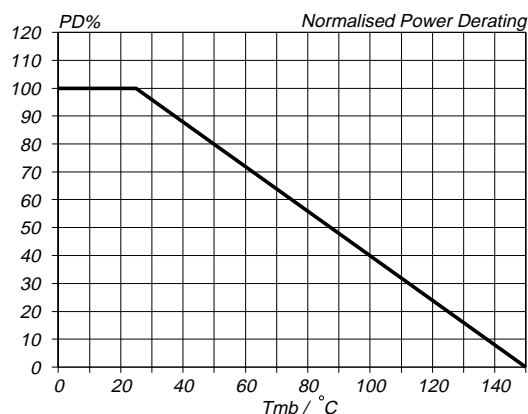


Fig.7. Normalised power dissipation.  
 $PD\% = 100 \cdot PD / PD_{25^\circ C} = f(T_{mb})$

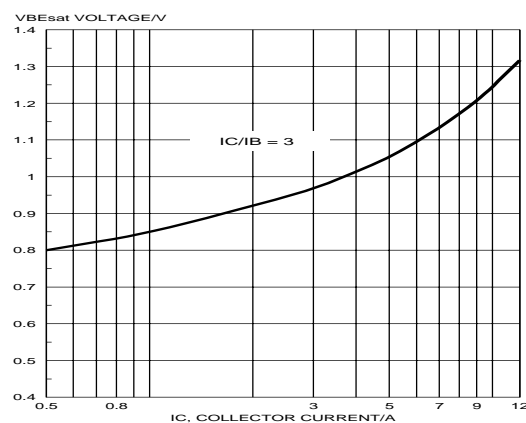


Fig.10. Base-Emitter saturation voltage.  
 Solid lines = typ values,  $V_{BEsat} = f(I_C)$ ; at  $I_C/I_B = 5$ .

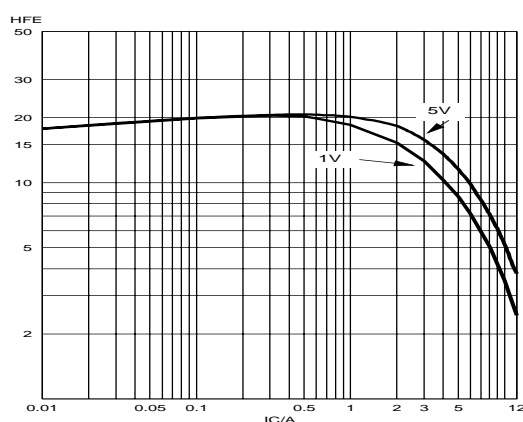


Fig.8. Typical DC current gain.  $h_{FE} = f(I_C)$   
 parameter  $V_{CE}$

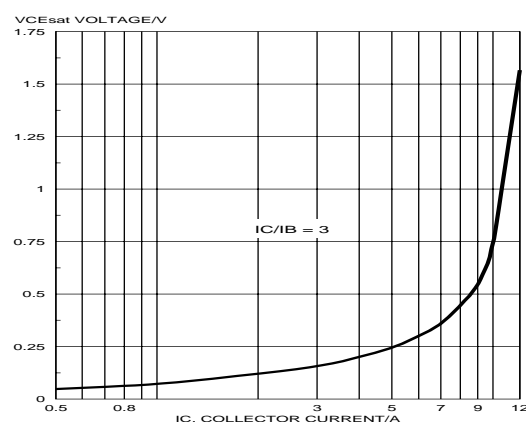


Fig.11. Collector-Emitter saturation voltage.  
 Solid lines = typ values,  $V_{CEsat} = f(I_C)$ ; at  $I_C/I_B = 5$ .

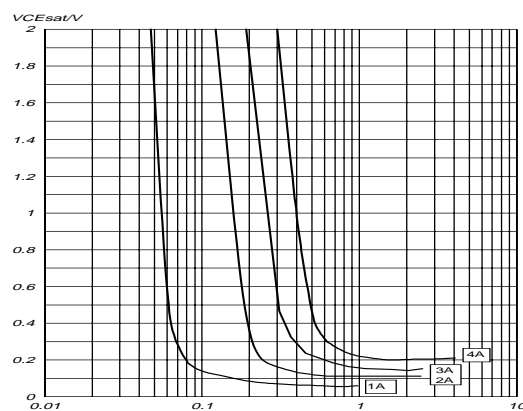


Fig.9. Collector-Emitter saturation voltage.  
 Solid lines = typ values,  $V_{CEsat} = f(I_B)$ ;  $T_J = 25^\circ C$ .

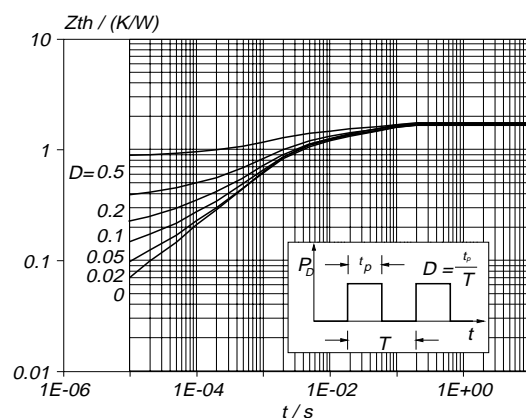


Fig.12. Transient thermal impedance.  
 $Z_{th j-mb} = f(t)$ ; parameter  $D = t_p/T$

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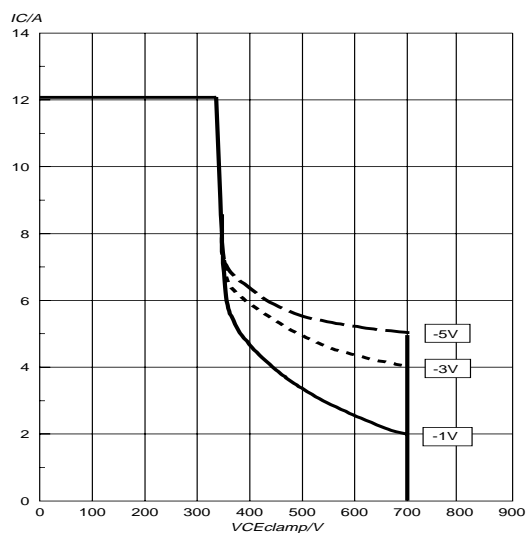


Fig.13. Reverse bias safe operating area ( $T_j < T_{jmax}$ ) for  $-V_{be} = 5V, 3V$  and  $1V$ .

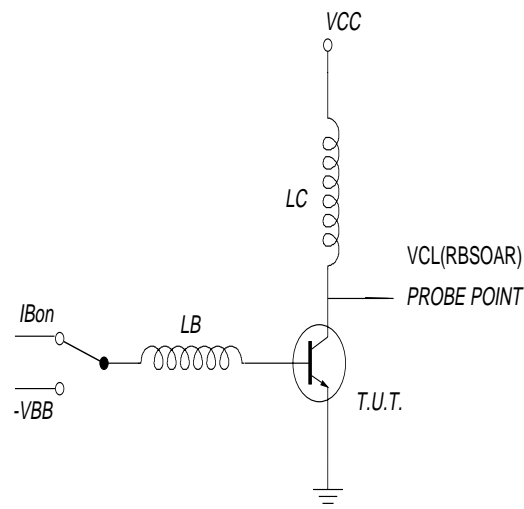


Fig.14. Test circuit for reverse bias safe operating area.

$$V_{clamp} < 700V; V_{cc} = 150V; -V_{be} = 5V, 3V \text{ \& } 1V; \\ L_B = 1\mu H; L_C = 200\mu H$$

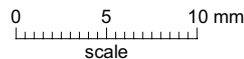
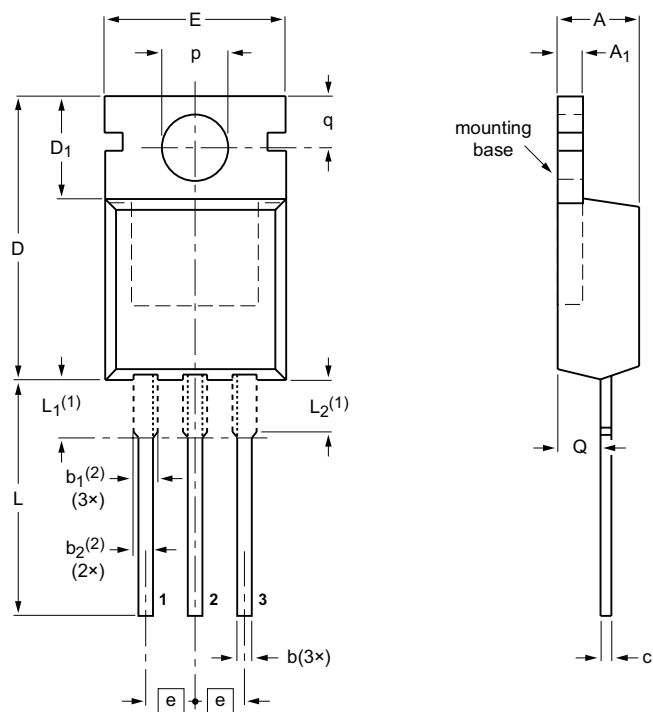
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MECHANICAL DATA

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB


SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> (1)	L <sub>2</sub> (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- Notes
- Lead shoulder designs may vary.
  - Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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